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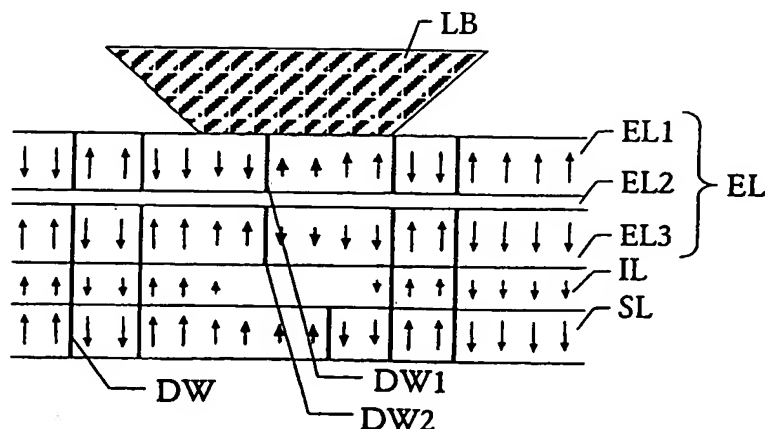
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(54) Title: **MAGNETO-OPTICAL RECORDING MEDIUM WITH ANTI-FERROMAGNETICALLY COUPLED DOMAIN-EXPANSION DOUBLE-LAYER STRUCTURE**



(57) Abstract: A magneto-optical recording medium and manufacturing method for such a medium, wherein a readout expansion layer (EL) consisting of a double- or bi-layer structures with anti-ferromagnetic layers, e.g. GdFeCo or TbFeCo, coupled over a relatively thin non-magnetic metallic layer, e.g. a Ru layer. Under influence of the temperature rise by the focussed spot of a readout radiation beam and the stray field from a storage layer (SL), the magnetization in the double-layer will switch from an anti-parallel to a parallel state. A main advantage of this layer structure is that it offers a symmetric readout response for up and down magnetization in the storage layer (SL) and can in principle be used without external readout field.